Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- · 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- · High immunity to false turn-on by dV/dt
- High voltage capability
- · Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only

3. Applications

- · Electronic thermostats
- General purpose motor controls
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; $\overline{\text{Fig. 1}}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$	-	-	8	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	-	65	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	-	71	А
Tj	junction temperature		-	-	125	°C
Static chara	acteristics				,	,
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	2	18	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	2	21	50	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	2	34	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
Dynamic char	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 535 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 20 V/ μ s; snubberless condition; gate open circuit; Fig. 12	-	14	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2	├	G sym051
3	G	gate		Symoor
mb	Т2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BTA208-800B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	8	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	65	Α
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	71	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	21	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

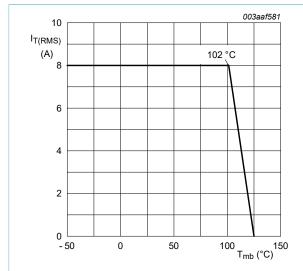


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

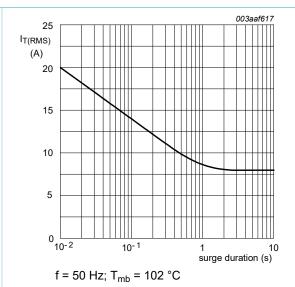


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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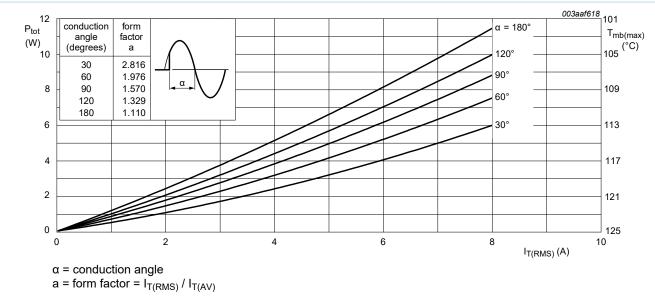


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

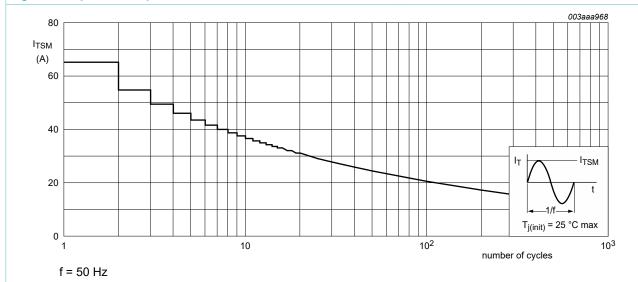
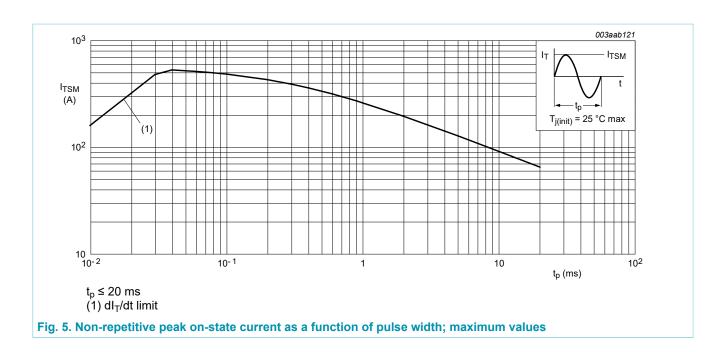


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 6	-	-	2	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

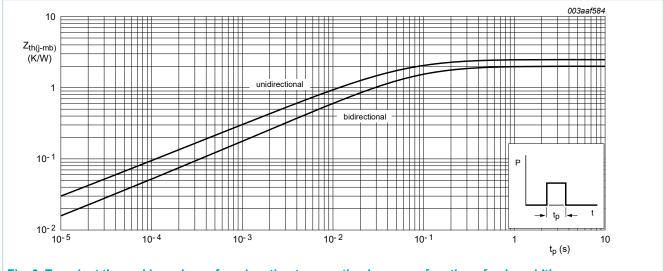


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	2	18	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	2	34	50	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	31	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	34	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	30	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics				1	,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 535 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 20 V/µs; snubberless condition; gate open circuit; Fig. 12	-	14	-	A/ms
t _{gt}	gate-controlled turn-on time	I_{TM} = 12 A; V_D = 800 V; I_G = 0.1 A; dI_G/dt = 5 A/ μ s	-	2	-	μs

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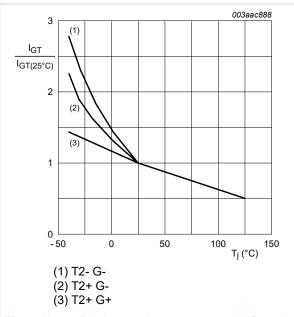


Fig. 7. Normalized gate trigger current as a function of junction temperature

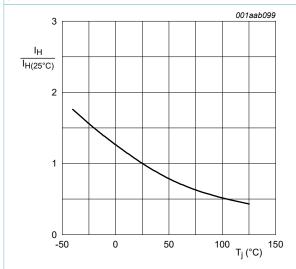


Fig. 9. Normalized holding current as a function of junction temperature

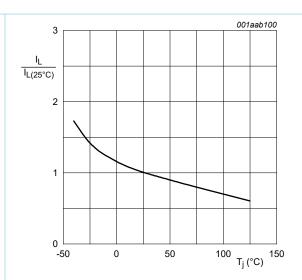
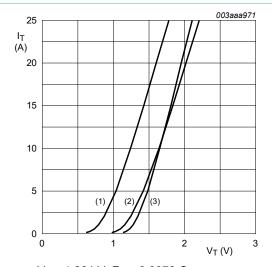


Fig. 8. Normalized latching current as a function of junction temperature



 V_o = 1.264 V; R_s = 0.0378 Ω

(1) $T_j = 125$ °C; typical values (2) $T_j = 125$ °C; maximum values (3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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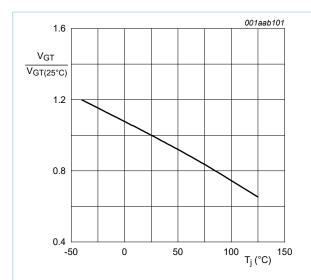


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

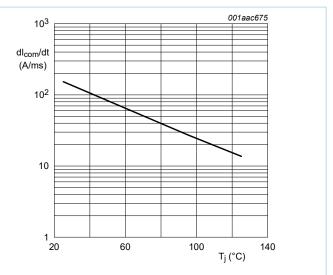
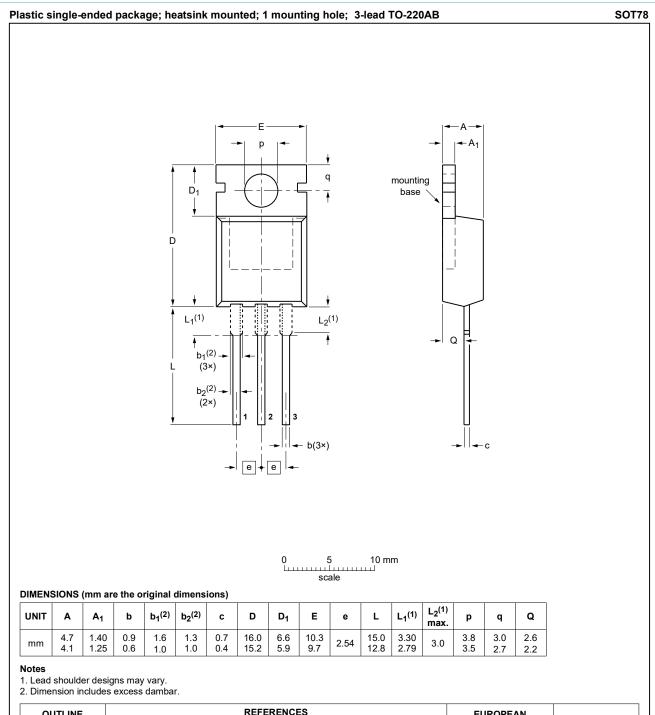


Fig. 12. Rate of rise of commutating current as a function of junction temperature; typical values

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10. Package outline



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13
					- 1	

Fig. 13. Package outline TO-220AB (SOT78)

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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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